Revision. 1

MOS FET

FK4B01120L

Panasonic

FK4B01120L

Single N-channel MOS FET

For Load switching circuits

■ Features

- Low Drain-source ON resistance:RDS(on) typ. = $17m\Omega(VGS = 2.5 V)$
- CSP (Chip Size Package)
- RoHS compliant (EU RoHS / MSL:Level 1 compliant)
- Marking Symbol: 1C

■ Packaging

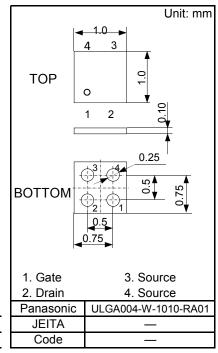
Embossed type (Thermo-compression sealing): 20 000 pcs / reel (standard)

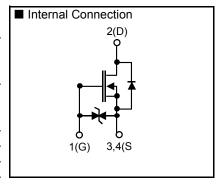
■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit			
Drain-Source Voltage	VDS	12	V			
Gate-Source Voltage	VGS	±8	V			
	ID1*1	3.9				
Drain Current	ID2*2	6.5	Α			
	ID3*3	7.9				
Peak Drain Current	IDp1*1*4	31	А			
	IDp2*2*4	52				
	IDp3 ^{*3*4}	63				
	PD1 ^{*1}	0.37	W			
Power Dissipation	PD2 ^{*2}	0.94				
	PD3 ^{*3}	1.5				
Channel Temperature	Tch	150	°C			
Operating Ambient Temperature	Topr	-40 ~ +85	°C			
Storage Temperature	Tstg	-55 ~ +150	°C			



- *2 FR4 board (25.4mm×25.4mm×t1.0mm), Full Cu
- *3 Ceramic substrate (70mm×70mm×t1.0mm)
- *4 $t = 10 \mu s$, Duty Cycle < 1%





Established : 2014-03-24 Revised : ###-##

MOS FET

FK4B01120L

■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Drain-Source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0	12			V	
Zero Gate Voltage Drain Current	IDSS	VDS = 12 V, VGS = 0			10	μA	
Gate-Source Leakage Current	IGSS	VGS = ±8 V, VDS = 0 V			±10	μA	
Gate Threshold Voltage	Vth	ID = 394 μA, VDS =10 V	0.3		1.0	V	
Drain-Source ON Resistance		ID = 1.5 A, VGS = 4.5 V		14	24	mΩ	
	RDS(on)	ID = 1.0 A, VGS = 2.5 V		17	27		
	T NDS(OII)	ID = 0.5 A, VGS = 1.8 V		21	36		
		ID = 0.25 A, VGS = 1.5 V		27	62		
Input Capacitance *1	Ciss	VDS = 10 V		490			
Output Capacitance *1	Coss	VGS = 0		184		pF	
Reverse Transfer Capacitance *1	Crss	f = 1MHz		128			
Turn-on delay time *1,*2	td(on)	VDD = 6 V		4.3			
Rise time *1,*2	tr	VGS = 0 to 4.5 V		3.7		ns	
Turn-off delay time *1,*2	td(off)	ID=1.0 A		235			
Fall time *1,*2	tf	1B-1.0 A		147			
Total Gate Charge *1	Qg	VDD = 6 V		7		nC	
Gate to Source Charge *1	Qgs	VGS = 4.5 V		1.4		nC	
Gate to Drain Miller Charge *1	Qgd	ID= 1.0 A		1.5		nC	
Body Diode Forward Voltage	VF(D-S)	IF = 0.2A, VGS = 0V		0.6	1.2	V	

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

■ Electrical State Discharge Characteristics

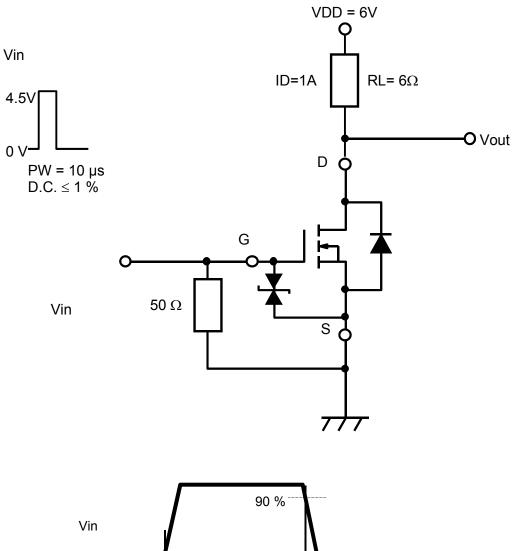
Standard	Test Type	Symbol	Conditions	Class	Value	Unit
AEC-Q101-001	Human body model	HBM	C = 100 pF, R = $1.5 \text{ k}\Omega$	H2	>2k to ≦ 4k	V
	Machine model	MM	C = 200 pF, R = 0 Ω	M2	>100 to \leq 200	V

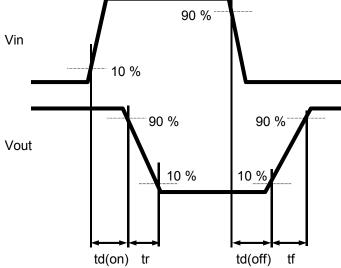
Established : 2014-03-24 Revised : ###-##-##

^{*1} Guaranteed by design, not subject to production testing

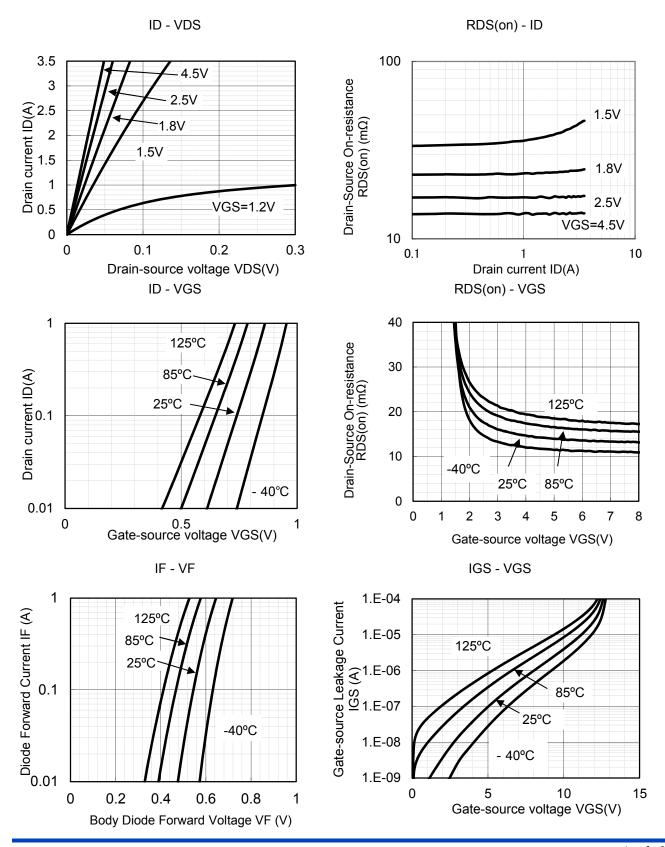
^{*2} Measurement circuit for Turn-on delay time / Rise time / Turn-off delay time / Fall time

Note2: Measurement circuit



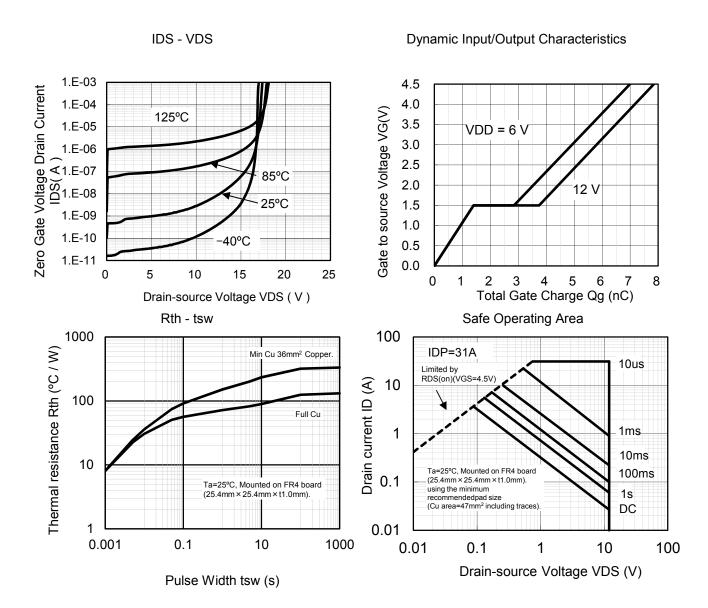


Established: 2014-03-24 Revised: ###-##



Page 4 of 6

Established : 2014-03-24 Revised : ###-##-##

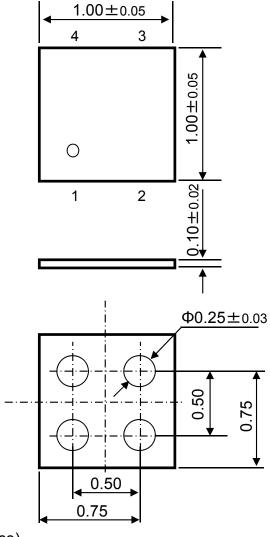


Established : 2014-03-24 Revised : ###-##

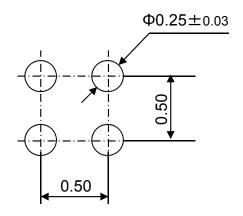
MOS FET FK4B01120L

■ ULGA004-W-1010-RA01

Unit: mm



■ Land Pattern (Reference)



Page 6 of 6

Established: 2014-03-24 Revised: ###-##-##

Request for your special attention and precautions in using the technical information and semiconductors described in this book

- (1) If any of the products or technical information described in this book is to be exported or provided to non-residents, the laws and regulations of the exporting country, especially, those with regard to security export control, must be observed.
- (2) The technical information described in this book is intended only to show the main characteristics and application circuit examples of the products. No license is granted in and to any intellectual property right or other right owned by Panasonic Corporation or any other company. Therefore, no responsibility is assumed by our company as to the infringement upon any such right owned by any other company which may arise as a result of the use of technical information de-scribed in this book.
- (3) The products described in this book are intended to be used for general applications (such as office equipment, communications equipment, measuring instruments and household appliances), or for specific applications as expressly stated in this book.
 - Please consult with our sales staff in advance for information on the following applications, moreover please exchange documents separately on terms of use etc.: Special applications (such as for in-vehicle equipment, airplanes, aerospace, automotive equipment, traffic signaling equipment, combustion equipment, medical equipment and safety devices) in which exceptional quality and reliability are required, or if the failure or malfunction of the products may directly jeopardize life or harm the human body.
 - Unless exchanging documents on terms of use etc. in advance, it is to be understood that our company shall not be held responsible for any damage incurred as a result of or in connection with your using the products described in this book for any special application.
- (4) The products and product specifications described in this book are subject to change without notice for modification and/or improvement. At the final stage of your design, purchasing, or use of the products, therefore, ask for the most upto-date Product Standards in advance to make sure that the latest specifications satisfy your requirements.
- (5) When designing your equipment, comply with the range of absolute maximum rating and the guaranteed operating conditions (operating power supply voltage and operating environment etc.). Especially, please be careful not to exceed the range of absolute maximum rating on the transient state, such as power-on, power-off and mode-switching. Otherwise, we will not be liable for any defect which may arise later in your equipment.
 Even when the products are used within the guaranteed values, take into the consideration of incidence of break down and failure mode, possible to occur to semiconductor products. Measures on the systems such as redundant design, arresting the spread of fire or preventing glitch are recommended in order to prevent physical injury, fire, social damages, for example, by using the products.
- (6) Comply with the instructions for use in order to prevent breakdown and characteristics change due to external factors (ESD, EOS, thermal stress and mechanical stress) at the time of handling, mounting or at customer's process. We do not guarantee quality for disassembled products or the product re-mounted after removing from the mounting board. When using products for which damp-proof packing is required, satisfy the conditions, such as shelf life and the elapsed time since first opening the packages.
- (7) When reselling products described in this book to other companies without our permission and receiving any claim of request from the resale destination, please understand that customers will bear the burden.
- (8) This book may be not reprinted or reproduced whether wholly or partially, without the prior written permission of our company.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Panasonic manufacturer:

Other Similar products are found below:

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201

JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DLE 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1

RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3 2SK2614(TE16L1,Q)